

To all our customers

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Renesas Technology Corp.  
Customer Support Dept.  
April 1, 2003

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Keep safety first in your circuit designs!

1. Renesas Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.

Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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# 2SK2007

Silicon N-Channel MOS FET

**RENESAS**

ADE-208-1339 (Z)  
1st. Edition  
Mar. 2001

## Application

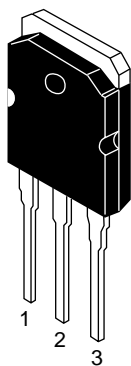
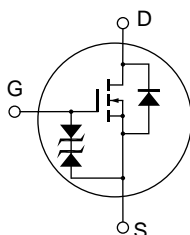
High speed power switching

## Features

- Low on-resistance
- High speed switching
- Low drive current
- No Secondary Breakdown
- Suitable for Switching regulator, DC - DC converter, Motor Control

## Outline

TO-3P



1. Gate
2. Drain  
(Flange)
3. Source

Absolute Maximum Ratings (Ta = 25°C)

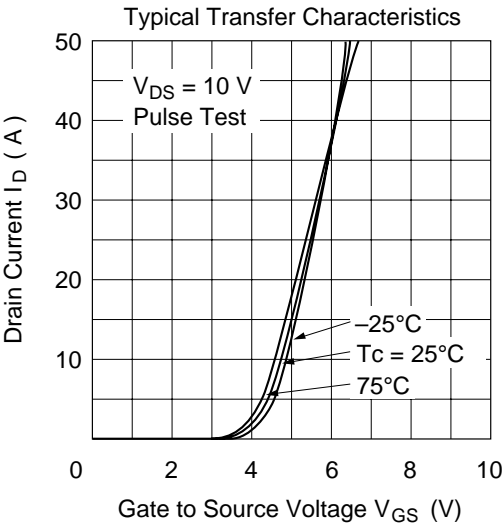
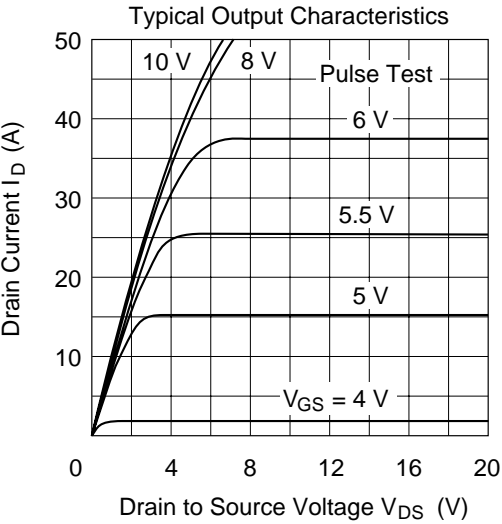
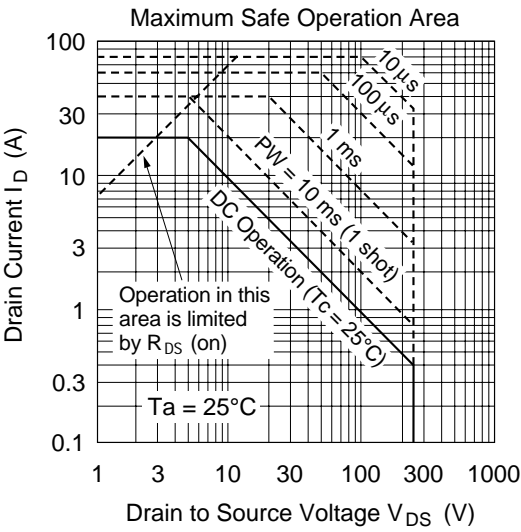
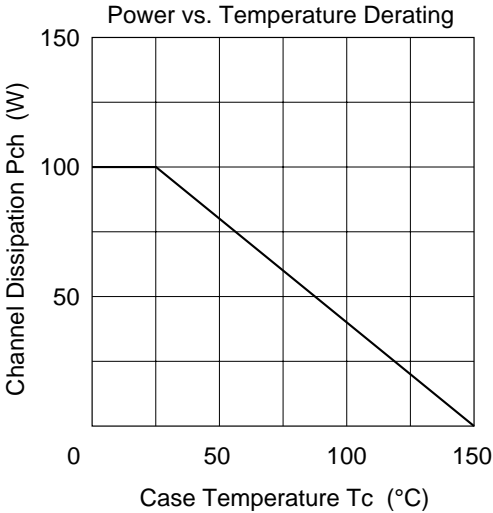
Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	250	V
Gate to source voltage	V <sub>GSS</sub>	±30	V
Drain current	I <sub>D</sub>	20	A
Drain peak current	I <sub>D(pulse)</sub> <sup>*1</sup>	80	A
Body to drain diode reverse drain current	I <sub>DR</sub>	20	A
Channel dissipation	Pch <sup>*2</sup>	100	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	−55 to +150	°C

Notes 1. PW 10 μs, duty cycle 1 %  
2. Value at Tc = 25°C

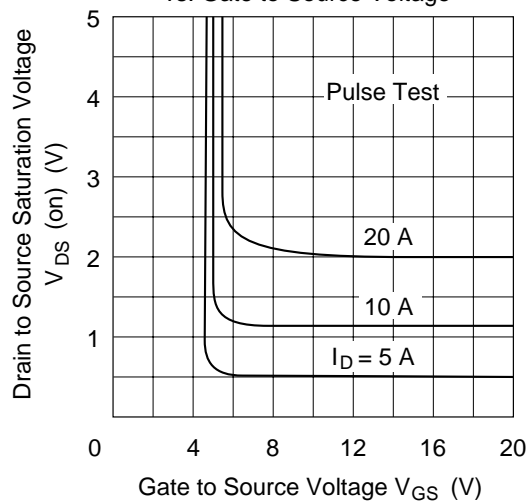
## Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	250	—	—	V	$I_D = 10 \text{ mA}$ , $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	$\pm 30$	—	—	V	$I_G = \pm 100 \text{ }\mu\text{A}$ , $V_{DS} = 0$
Gate to source leak current	$I_{GSS}$	—	—	$\pm 10$	$\mu\text{A}$	$V_{GS} = \pm 25 \text{ V}$ , $V_{DS} = 0$
Zero gate voltage drain current	$I_{DSS}$	—	—	250	$\mu\text{A}$	$V_{DS} = 200 \text{ V}$ , $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	2.0	—	3.0	V	$I_D = 1 \text{ mA}$ , $V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.12	0.15		$I_D = 10 \text{ A}$ $V_{GS} = 10 \text{ V}^{*1}$
Forward transfer admittance	$ y_{fs} $	9.0	14	—	S	$I_D = 10 \text{ A}$ $V_{DS} = 10 \text{ V}^{*1}$
Input capacitance	$C_{iss}$	—	2340	—	pF	$V_{DS} = 10 \text{ V}$
Output capacitance	$C_{oss}$	—	1000	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	$C_{rss}$	—	160	—	pF	$f = 1 \text{ MHz}$
Turn-on delay time	$t_{d(on)}$	—	30	—	ns	$I_D = 10 \text{ A}$
Rise time	$t_r$	—	125	—	ns	$V_{GS} = 10 \text{ V}$
Turn-off delay time	$t_{d(off)}$	—	190	—	ns	$R_L = 3$
Fall time	$t_f$	—	100	—	ns	
Body to drain diode forward voltage	$V_{DF}$	—	1.2	—	V	$I_F = 20 \text{ A}$ , $V_{GS} = 0$
Body to drain diode reverse recovery time	$t_{rr}$	—	120	—	ns	$I_F = 20 \text{ A}$ , $V_{GS} = 0$ , $di_F / dt = 100 \text{ A} / \mu\text{s}$

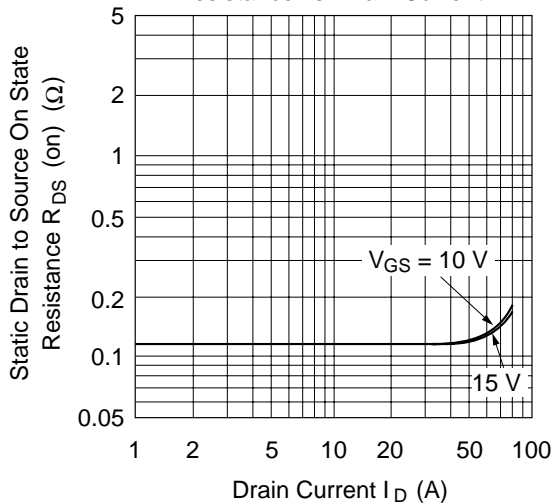
Note 1. Pulse Test



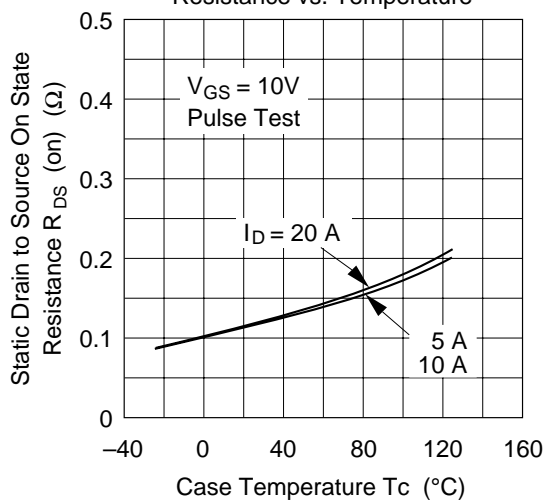
Drain to Source Saturation Voltage  
vs. Gate to Source Voltage



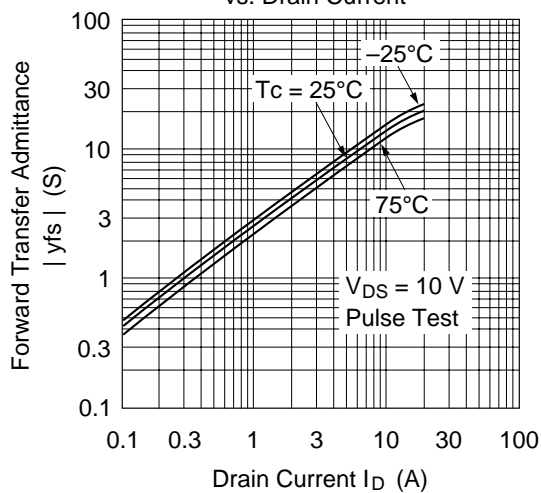
Static Drain to Source On State  
Resistance vs. Drain Current

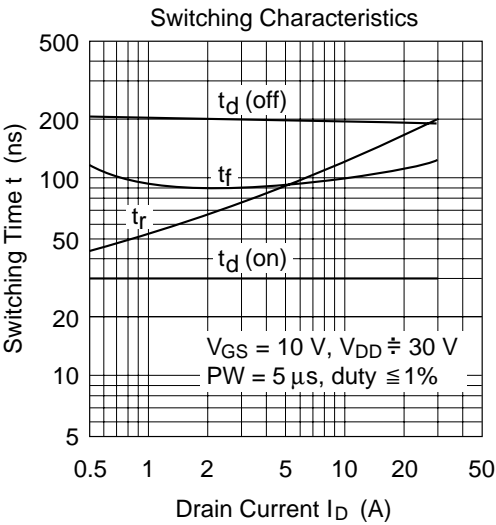
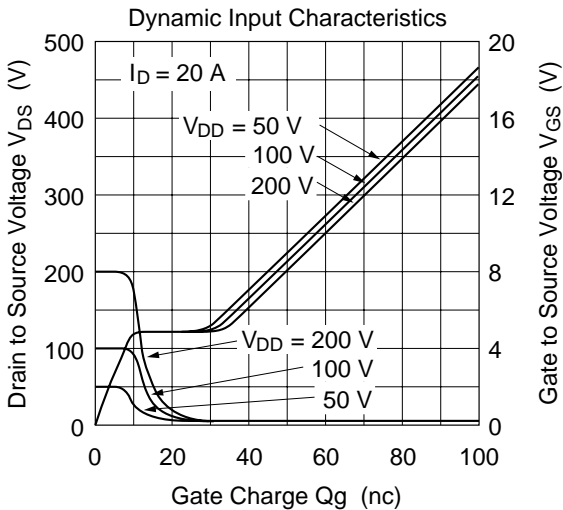
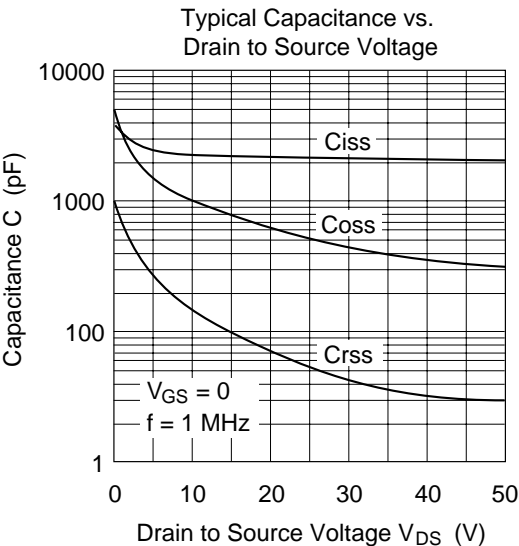
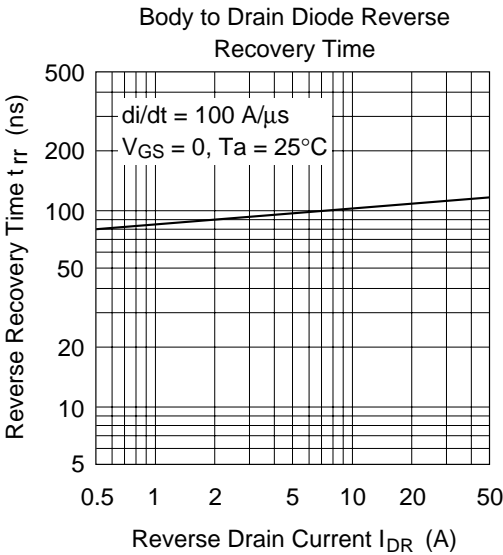


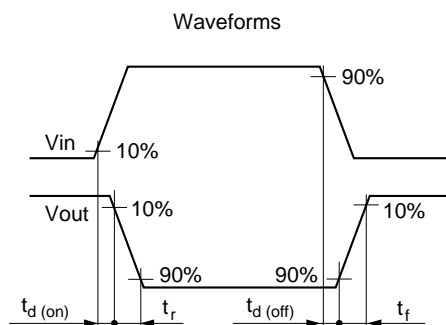
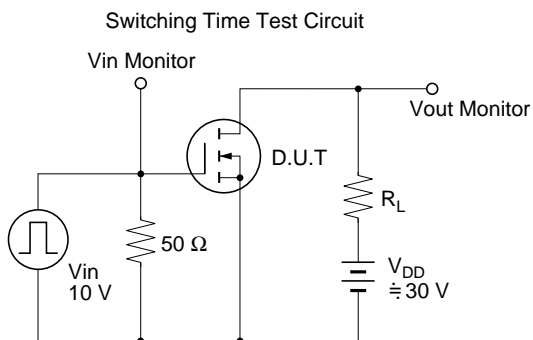
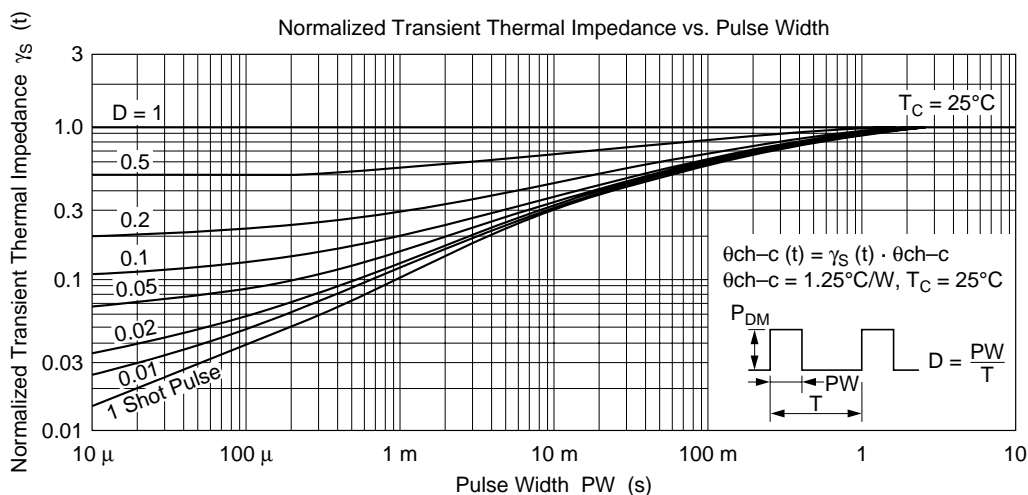
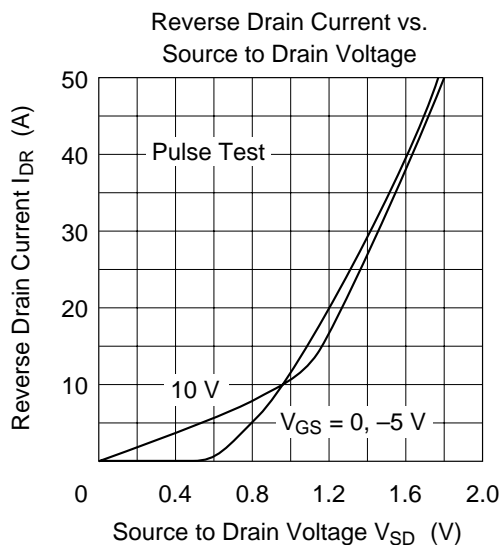
Static Drain to Source On State  
Resistance vs. Temperature



Forward Transfer Admittance  
vs. Drain Current

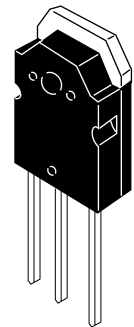
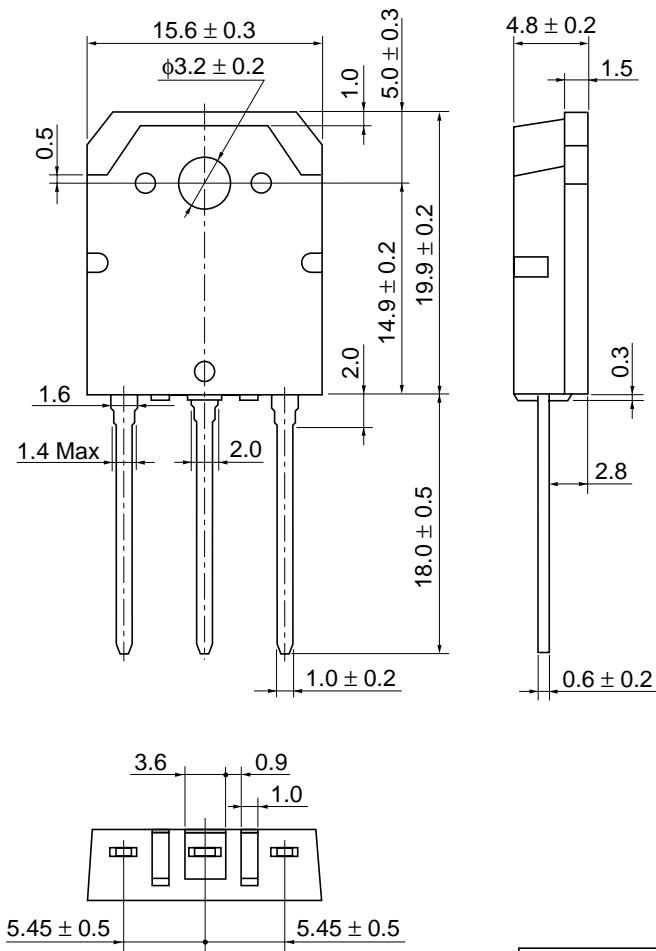






Package Dimensions

As of January, 2001  
Unit: mm



Hitachi Code	TO-3P
JEDEC	—
EIAJ	Conforms
Mass (reference value)	5.0 g

## Cautions

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